

**N-channel 400 V, 3 Ω typ., 1.8 A
SuperMESH3™ Power MOSFET in a SOT-223 package**

Datasheet - production data

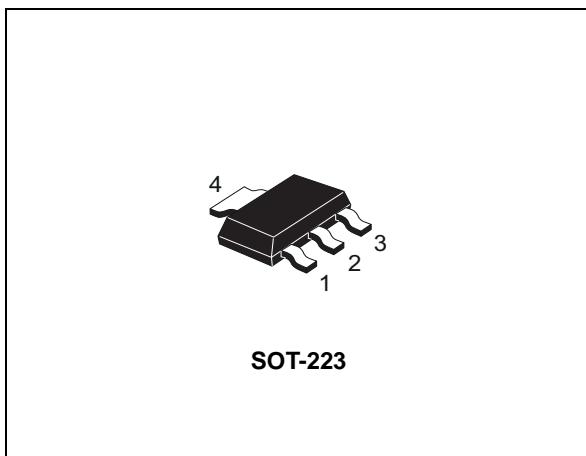
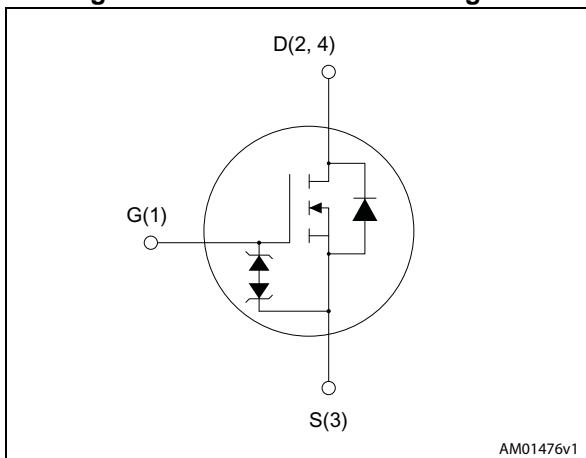


Figure 1. Internal schematic diagram



Features

| Order code | V_{DS} | $R_{DS(on)}$ max | I_D | P_{TOT} |
|------------|----------|---------------------|-------|-----------|
| STN3N40K3 | 400V | 3.4 Ω | 1.8 A | 3.3W |

- 100% avalanche tested
- Extremely high dv/dt capability
- Gate charge minimized
- Very low intrinsic capacitance
- Improved diode reverse recovery characteristics
- Zener-protected

Application

- Switching applications

Description

This SuperMESH3™ Power MOSFET is the result of improvements applied to STMicroelectronics' SuperMESH™ technology, combined with a new optimized vertical structure. This device boasts an extremely low on-resistance, superior dynamic performance and high avalanche capability, rendering it suitable for the most demanding applications.

Table 1. Device summary

| Order code | Marking | Package | Packaging |
|------------|---------|---------|---------------|
| STN3N40K3 | 3N40K3 | SOT-223 | Tape and reel |

Contents

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1 Electrical ratings

Table 2. Absolute maximum ratings

| Symbol | Parameter | Value | Unit |
|--------------------|--|--------------------|------------------|
| V_{DS} | Drain source voltage | 400 | V |
| V_{GS} | Gate-source voltage | ± 30 | V |
| I_D | Drain current continuous $T_C = 25^\circ\text{C}$ | 1.8 ⁽¹⁾ | A |
| I_D | Drain current continuous $T_C = 100^\circ\text{C}$ | 1 ⁽¹⁾ | A |
| $I_{DM}^{(2)}$ | Drain current pulsed | 7.2 | A |
| $I_{AR}^{(3)}$ | Avalanche current, repetitive or not repetitive | 0.6 | A |
| $E_{AS}^{(4)}$ | Single pulse avalanche energy | 45 | mJ |
| P_{TOT} | Total dissipation at $T_{amb} = 25^\circ\text{C}$ | 3.3 | W |
| $dv/dt^{(5)}$ | Peak diode recovery voltage slope | 12 | V/ns |
| E_{SD} | Gate-source human body model ($R = 1.5 \text{ k}\Omega$, $C = 100 \text{ pF}$) | 1 | kV |
| T_j T_{stg} | Operating junction temperature Storage temperature | -55 to 150 | $^\circ\text{C}$ |

1. Drain current limited by maximum junction temperature.
2. Pulse width limited by safe operating area.
3. Pulse width limited by T_{Jmax} .
4. Starting $T_j = 25^\circ\text{C}$, $I_D = I_{AR}$, $V_{DD} = 50 \text{ V}$.
5. $I_{sd} \leq 1.8 \text{ A}$, $di/dt \leq 400 \text{ A}/\mu\text{s}$, $V_{DD} \leq 80\% V_{(BR)DSS}$.

Table 3. Thermal data

| Symbol | Parameter | Value | Unit |
|---------------------|--------------------------------------|-------|---------------------------|
| $R_{thj-amb}^{(1)}$ | Thermal resistance junction-amb max. | 37.9 | $^\circ\text{C}/\text{W}$ |

1. When mounted on FR-4 board of 1 inch², 2oz Cu, $t < 30 \text{ s}$

2 Electrical characteristics

($T_{case} = 25^\circ C$ unless otherwise specified)

Table 4. On /off states

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|---------------|-----------------------------------|---|------|------|----------|---------------|
| $V_{(BR)DSS}$ | Drain-source breakdown voltage | $I_D = 1 \text{ mA}, V_{GS} = 0$ | 400 | | | V |
| I_{DSS} | Zero gate voltage drain current | $V_{GS} = 0, V_{DS} = 400 \text{ V}$ | | | 1 | μA |
| | | $V_{GS} = 0, V_{DS} = 400 \text{ V}, T_C = 125^\circ C$ | | | 50 | μA |
| I_{GSS} | Gate-body leakage current | $V_{DS} = 0, V_{GS} = \pm 20 \text{ V}$ | | | ± 10 | μA |
| $V_{GS(th)}$ | Gate threshold voltage | $V_{GS} = V_{DS}, I_D = 50 \mu\text{A}$ | 3 | 3.75 | 4.5 | V |
| $R_{DS(on)}$ | Static drain-source on resistance | $V_{GS} = 10 \text{ V}, I_D = 0.6 \text{ A}$ | | 3.1 | 3.4 | Ω |

Table 5. Dynamic

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|---------------------|--|--|------|------|------|----------|
| C_{iss} | Input capacitance | $V_{DS} = 50 \text{ V}, f = 1 \text{ MHz}, V_{GS} = 0$ | - | 165 | - | pF |
| C_{oss} | Output capacitance | | - | 17 | - | pF |
| C_{rss} | Reverse transfer capacitance | | - | 3 | - | pF |
| $C_{oss(er)}^{(1)}$ | Equivalent output capacitance energy related | $V_{DS} = 0 \text{ to } 320 \text{ V}, V_{GS} = 0$ | - | 9 | - | pF |
| $C_{oss(tr)}^{(2)}$ | Equivalent output capacitance time related | | - | 14 | - | pF |
| R_g | Intrinsic gate resistance | $f=1 \text{ MHz open drain}$ | - | 10 | - | Ω |
| Q_g | Total gate charge | $V_{DD} = 320 \text{ V}, I_D = 1.8 \text{ A}, V_{GS} = 10 \text{ V}$ (see Figure 18) | - | 11 | - | nC |
| Q_{gs} | Gate-source charge | | - | 2 | - | nC |
| Q_{gd} | Gate-drain charge | | - | 7 | - | nC |

1. Is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}
2. Is defined as a constant equivalent capacitance giving the same storage energy as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}

Table 6. Switching times

| Symbol | Parameter | Test conditions | Min. | Typ. | Max | Unit |
|--------------|---------------------|--|------|------|-----|------|
| $t_{d(on)}$ | Turn on delay time | $V_{DD} = 200 \text{ V}, I_D = 0.6, R_G = 4.7 \Omega, V_{GS} = 10 \text{ V}$ (see Figure 17) | - | 7 | - | ns |
| t_r | Rise time | | - | 8 | - | ns |
| $t_{d(off)}$ | Turn off delay time | | - | 18 | - | ns |
| t_f | Fall time | | - | 14 | - | ns |

Table 7. Source drain diode

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|-----------------|-------------------------------|--|------|------|------|------|
| I_{SD} | Source-drain current | | - | | 1.8 | A |
| $I_{SDM}^{(1)}$ | Source-drain current (pulsed) | | - | | 7.2 | A |
| $V_{SD}^{(2)}$ | Forward on voltage | $I_{SD} = 0.6 \text{ A}, V_{GS} = 0$ | - | | 1.5 | V |
| t_{rr} | Reverse recovery time | $I_{SD} = 1.8 \text{ A}, di/dt = 100 \text{ A}/\mu\text{s}$ $V_{DD} = 60 \text{ V}$ (see Figure 20) | - | 145 | | ns |
| Q_r | Reverse recovery charge | | - | 490 | | nC |
| I_{RRM} | Reverse recovery current | | - | 7 | | A |
| t_{rr} | Reverse recovery time | $I_{SD} = 1.8 \text{ A}, di/dt = 100 \text{ A}/\mu\text{s}$ $V_{DD} = 60 \text{ V}, T_j = 150 \text{ }^\circ\text{C}$ (see Figure 20) | - | 166 | | ns |
| Q_{rr} | Reverse recovery charge | | - | 580 | | nC |
| I_{RRM} | Reverse recovery current | | - | 7 | | A |

1. Pulse width limited by safe operating area.
2. Pulsed: pulse duration = 300 μs , duty cycle 1.5%

2.1 Electrical characteristics

Figure 2. Safe operating area

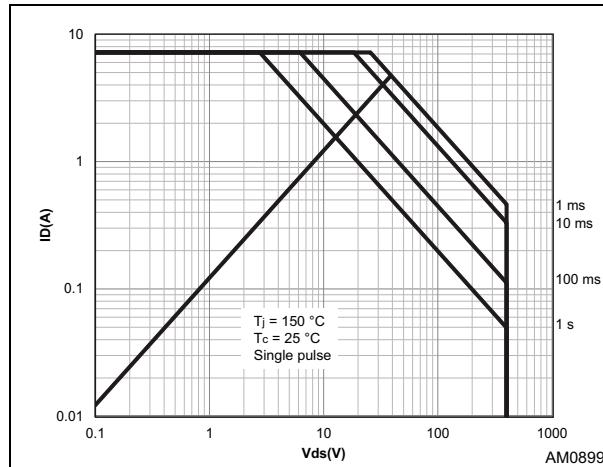


Figure 3. Thermal impedance

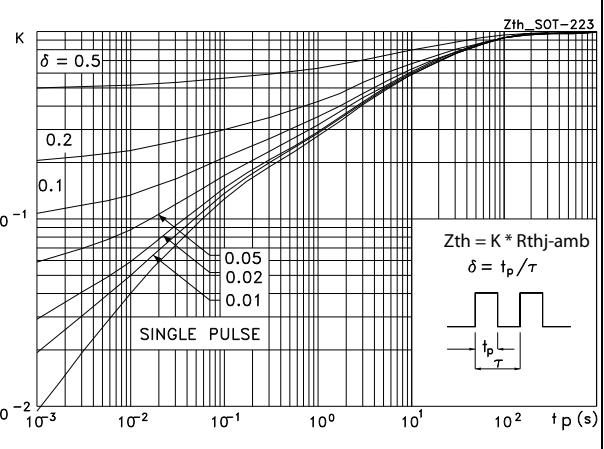


Figure 4. Output characteristics

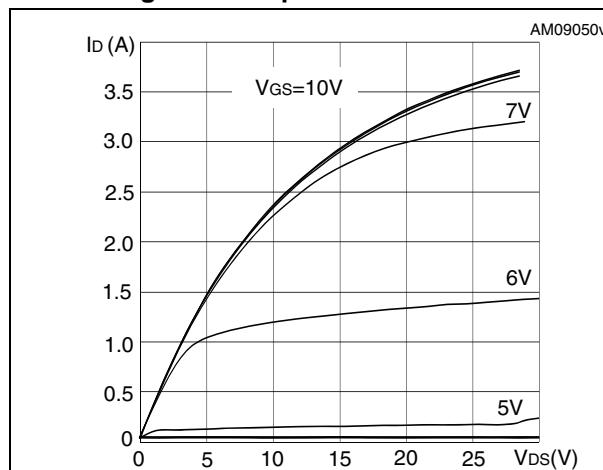


Figure 5. Transfer characteristics

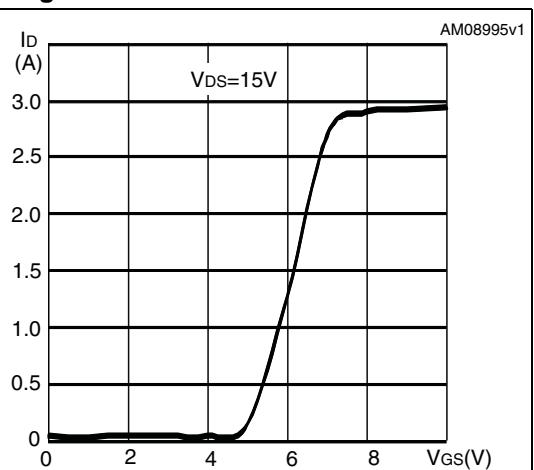


Figure 6. Gate charge vs gate-source voltage

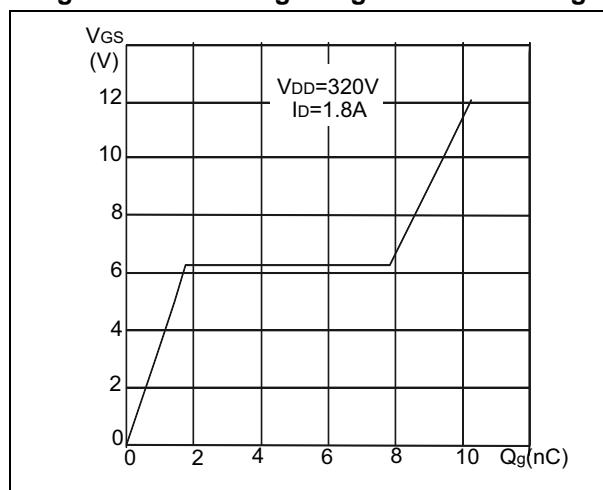


Figure 7. Static drain-source on resistance

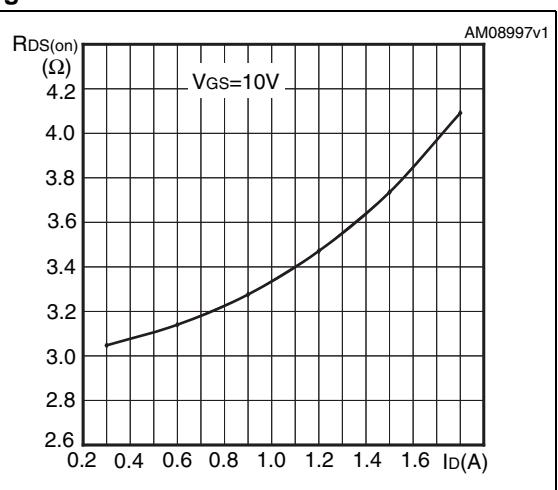


Figure 8. Capacitance variations

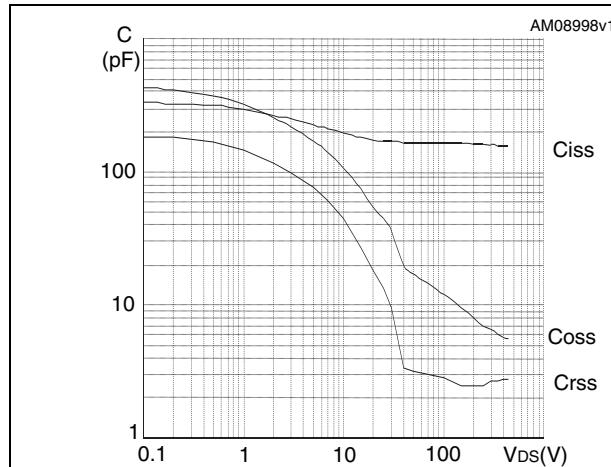


Figure 9. Output capacitance stored energy

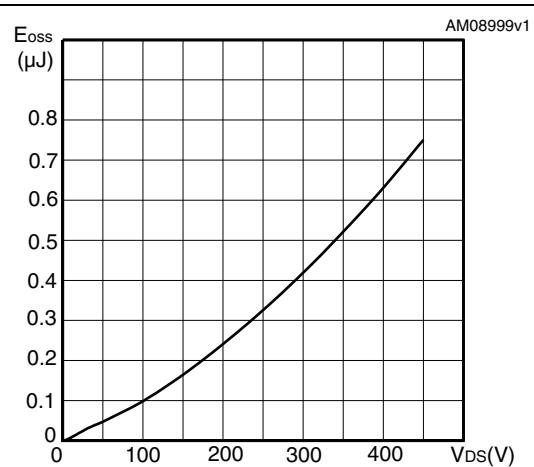


Figure 10. Normalized gate threshold voltage vs. temperature

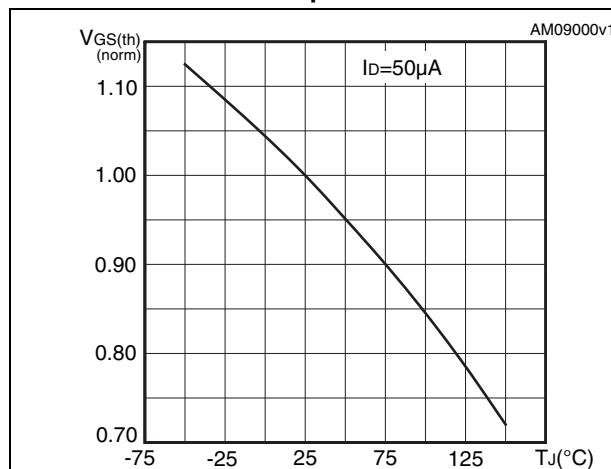


Figure 11. Normalized on resistance vs. temperature

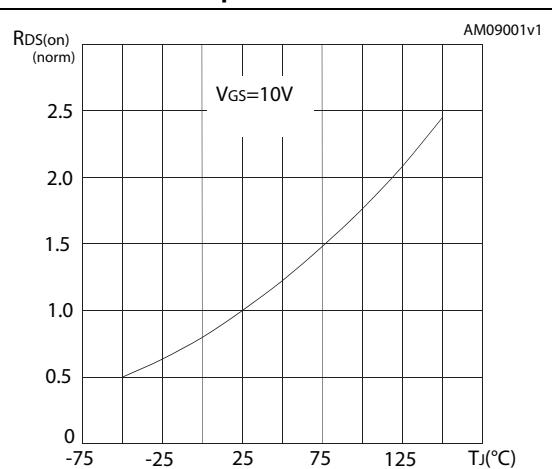
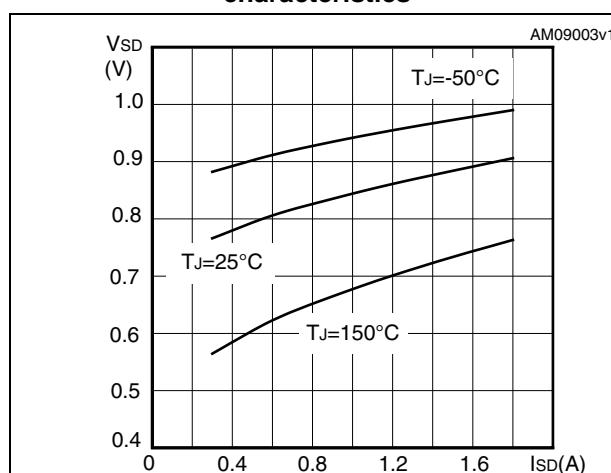
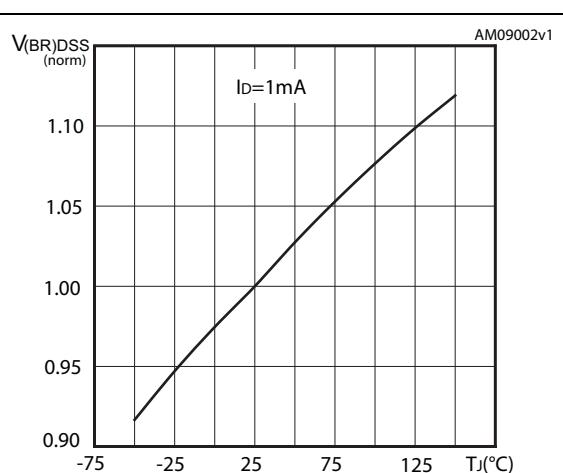
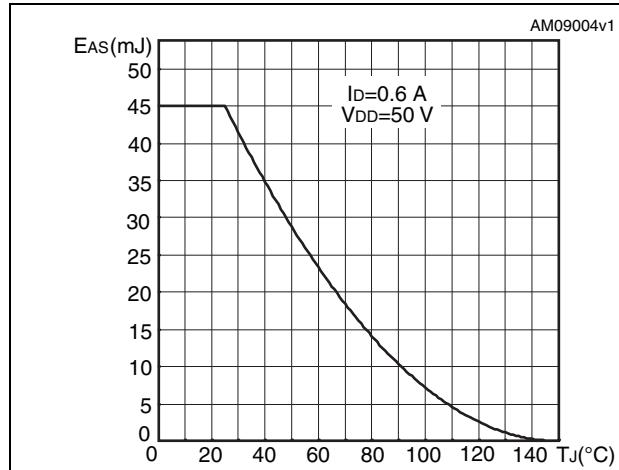


Figure 12. Source-drain diode forward characteristics

Figure 13. Normalized $V_{(BR)DSS}$ vs. temperature

**Figure 14. Maximum avalanche energy vs.
starting T_j**



3 Test circuits

Figure 15. Switching times test circuit for resistive load

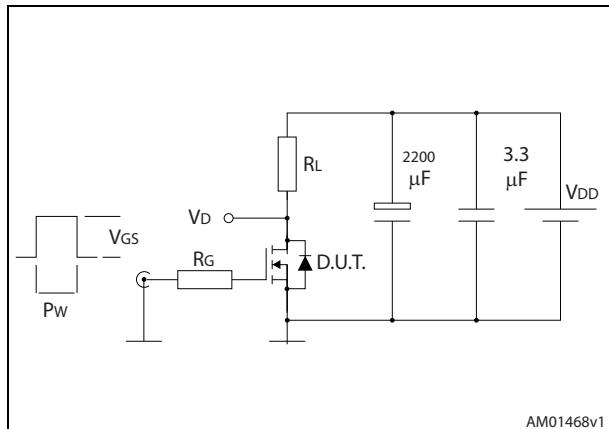


Figure 16. Gate charge test circuit

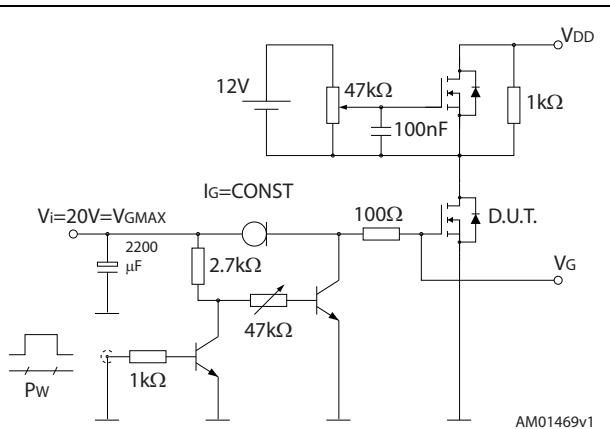


Figure 17. Switching times test circuit for resistive load

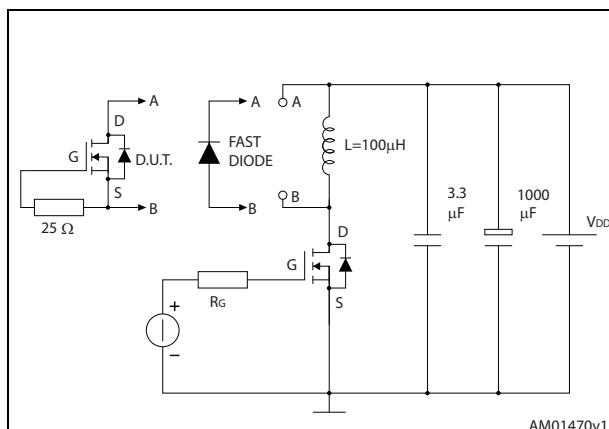


Figure 18. Gate charge test circuit

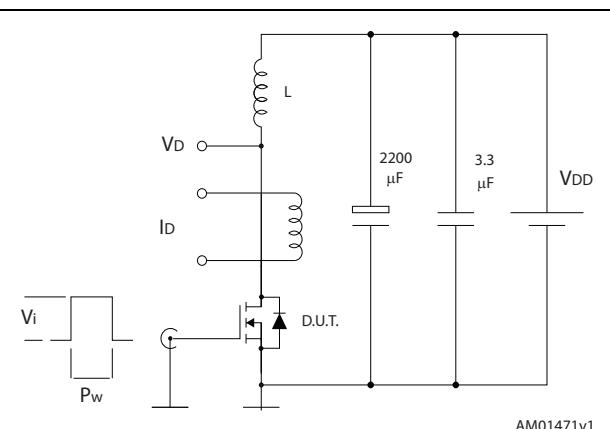


Figure 19. Unclamped inductive waveform

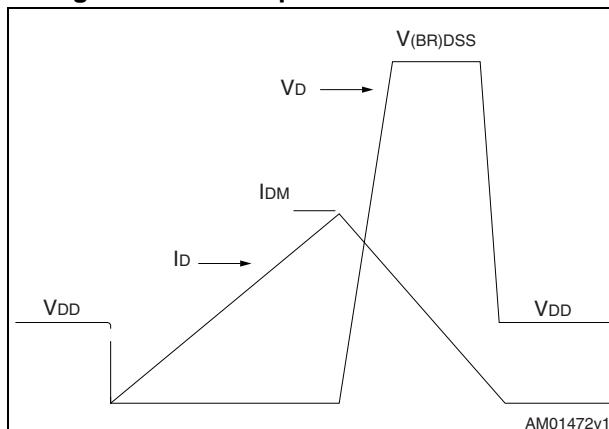
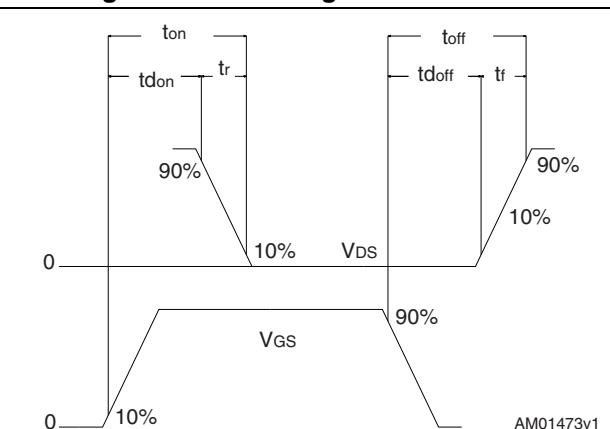


Figure 20. Switching time waveform



4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com.
ECOPACK is an ST trademark.

Figure 21. SOT-223 mechanical data drawing

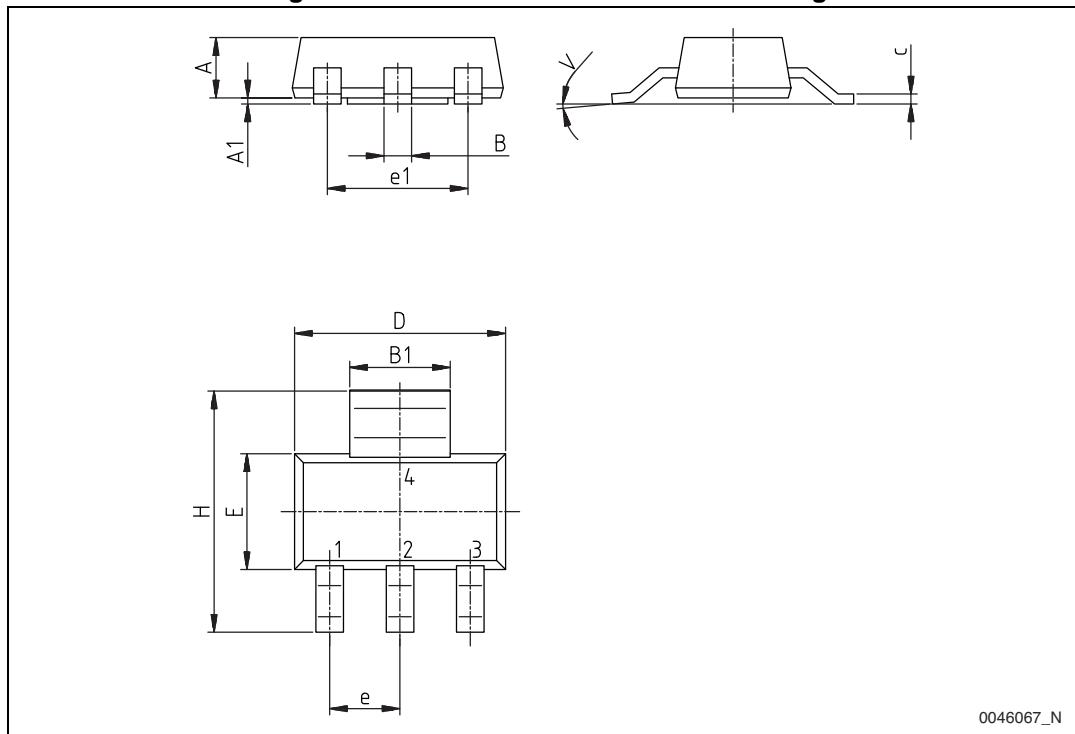
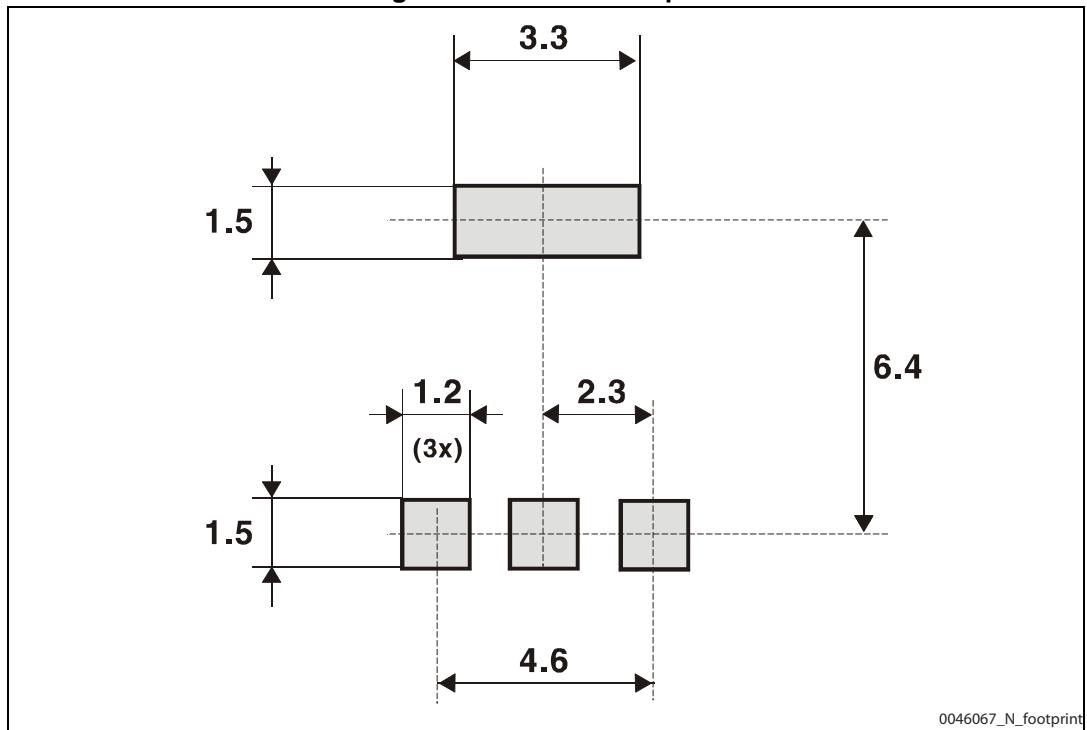


Table 8. SOT-223 mechanical data

| Dim. | mm | | |
|------|------|------|------|
| | Min. | Typ. | Max. |
| A | | | 1.80 |
| A1 | 0.02 | | 0.10 |
| B | 0.60 | 0.70 | 0.85 |
| B1 | 2.9 | 3.0 | 3.15 |
| c | 0.24 | 0.26 | 0.35 |
| D | 6.30 | 6.50 | 6.70 |
| e | | 2.30 | 6.70 |
| e1 | | 4.60 | |
| E | 3.30 | 3.50 | 3.70 |
| H | 6.70 | 7.0 | 7.30 |
| V | | | 10° |

Figure 22. SOT-223 footprint



5 Revision history

Table 9. Document revision history

| Date | Revision | Changes |
|-------------|----------|--|
| 29-Jun-2010 | 1 | First release. |
| 08-Apr-2011 | 2 | Document status promoted from preliminary data to datasheet. |
| 06-Jun-2014 | 3 | Updated silhouette, features and Figure 1: Internal schematic diagram in cover page. Updated Table 2: Absolute maximum ratings , Table 3: Thermal data , and Table 4: On /off states . Updated Figure 2: Safe operating area and Figure 6: Gate charge vs gate-source voltage . Updated Section 4: Package mechanical data . Minor text changes. |

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